

**EE6320 RF Integrated Circuits**  
**Project: PA Design**

**PA Performance Summary Table**

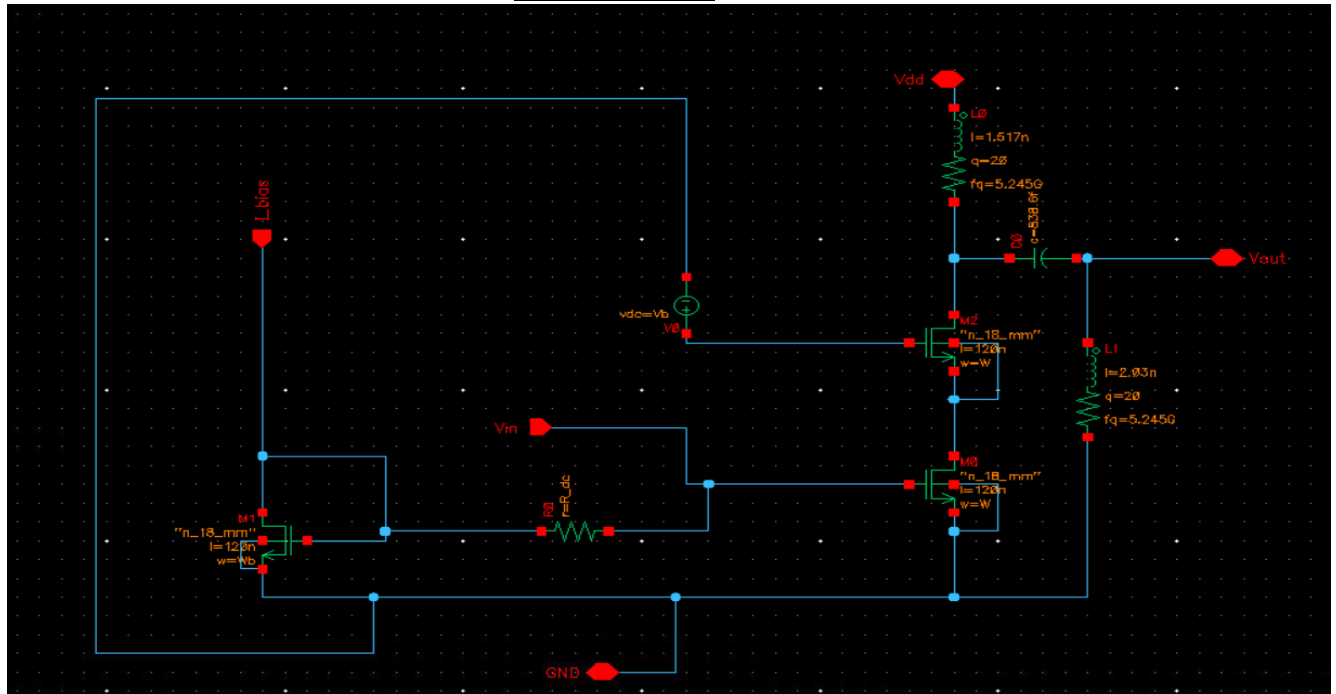
Design Parameter	Design Metric	Performance	Specification
Output P1dB	$f_o = 5.17 \text{ GHz}$	10.2609	$\geq +10 \text{ dBm}$
	$f_o = 5.245 \text{ GHz}$	10.2793	$\geq +10 \text{ dBm}$
	$f_o = 5.32 \text{ GHz}$	10.2963	$\geq +10 \text{ dBm}$
AM-PM Deviation (at P1dB)	$f_o = 5.17 \text{ GHz}$	1.3 deg	$\leq 5 \text{ degrees}$
	$f_o = 5.245 \text{ GHz}$	1.3 deg	$\leq 5 \text{ degrees}$
	$f_o = 5.32 \text{ GHz}$	1.3 deg	$\leq 5 \text{ degrees}$
Voltage Gain (from Gate to Drain)	$f_o = 5.17 \text{ GHz}$	10.65	$\geq 2$
	$f_o = 5.245 \text{ GHz}$	10.61	$\geq 2$
	$f_o = 5.32 \text{ GHz}$	10.58	$\geq 2$
Power (at 5.245 GHz)	PA Average Consumption (excluding bias)	27.156 mW	Minimize
	Bias Circuit Consumption	27.1 uW	Minimize
Other	Sum of all Capacitances (including ac coupling)	20.838p	-
	Inductance Used	3.7	-
	Device Width	1.4mm	-

	Simulator Used	Virtuoso	-
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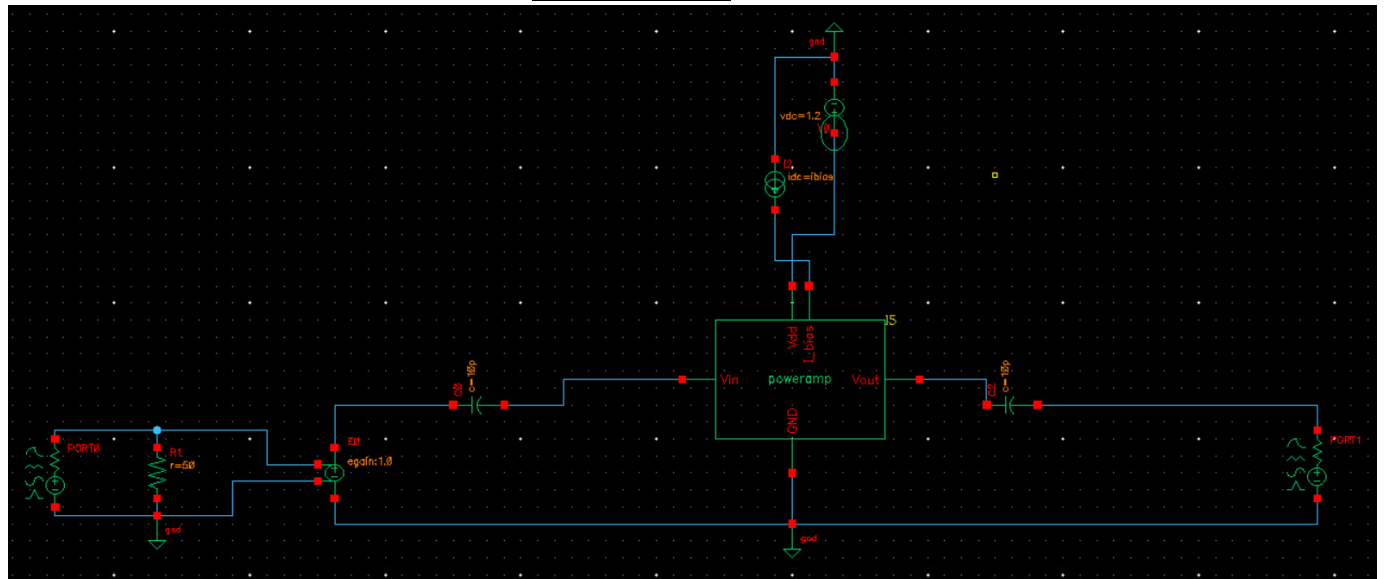
**Name:** Pragadeeswaran Kannan

**Roll No:** EE21B103

### PA Schematic



### PA Testbench

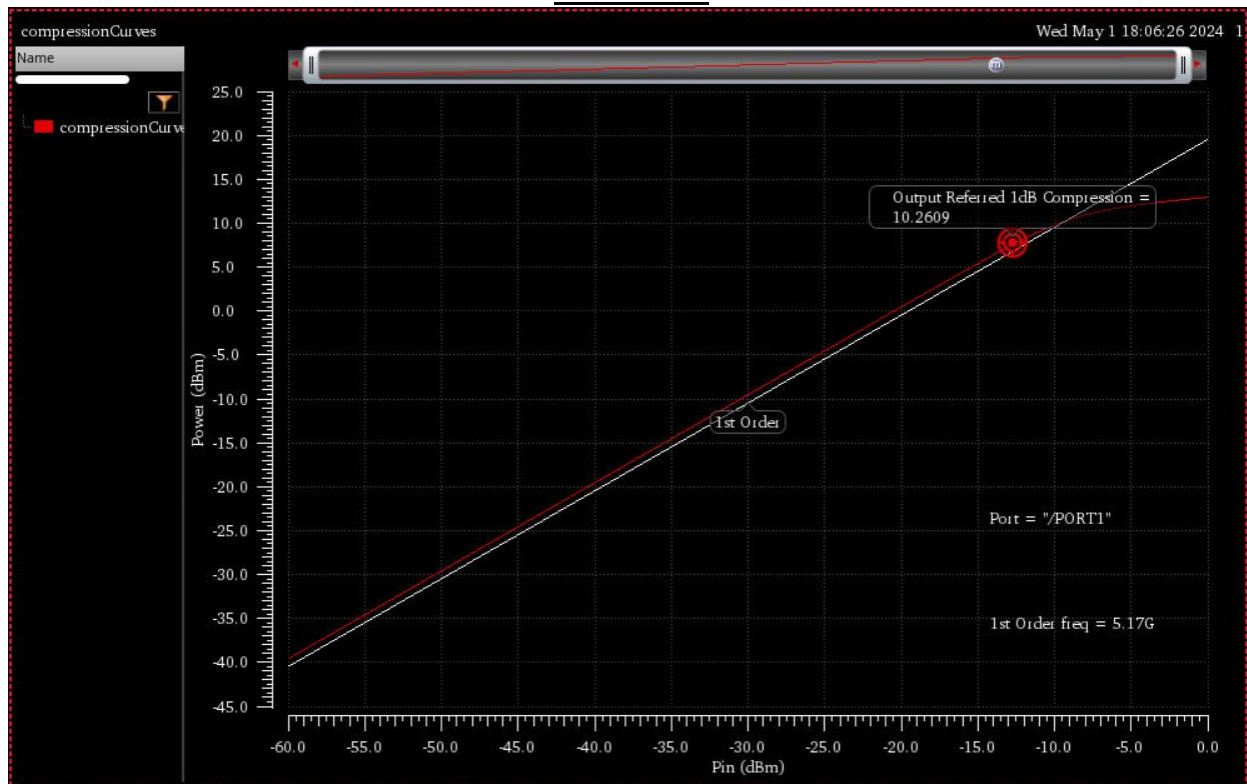


### Component Values Table

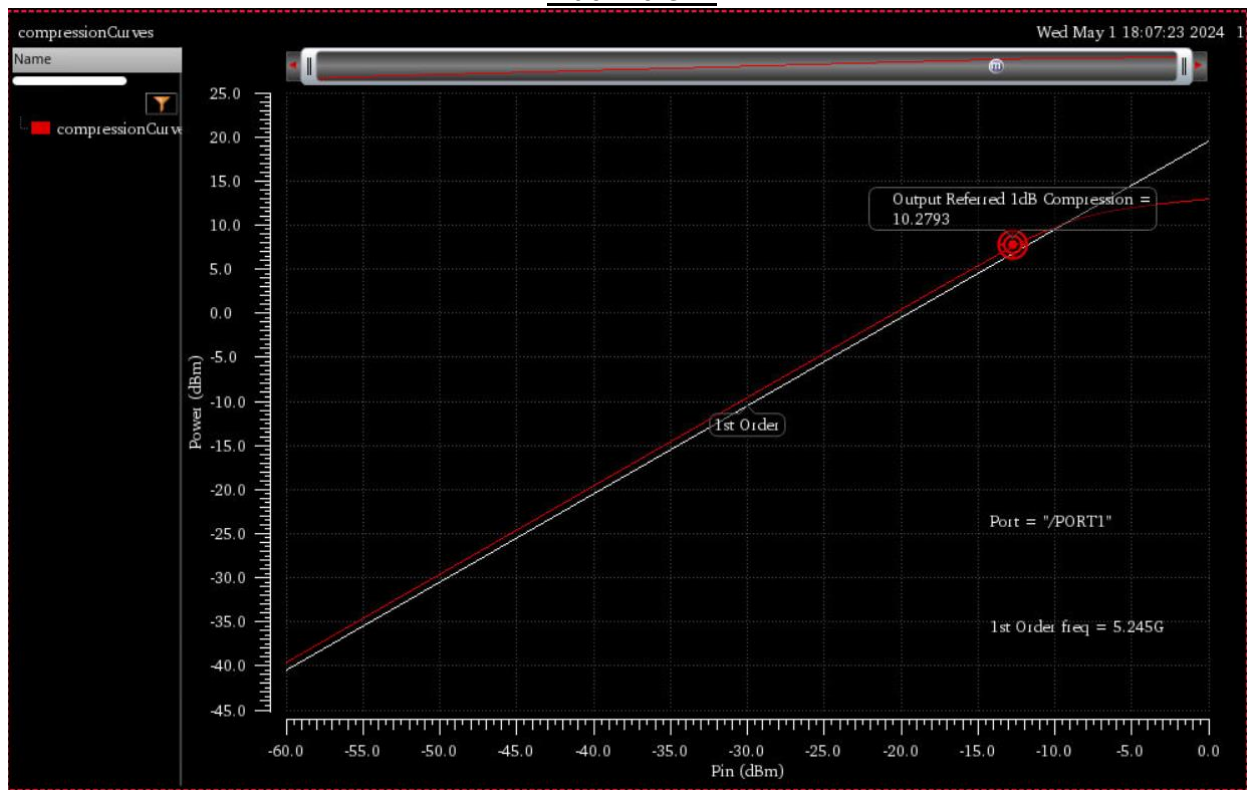
(W, L) MOS Amplifier = 1.4 mm, 120nm	(L, C, L2) Drain Tank = 1.517n, 868.3f, 2.03n
(W, L) Current Mirror MOS = 2.7um, 120nm	Bias Current = 50u
R_bias = 1 MΩ, C_coupling = 10p	V_DD = 1.2V , R_load = 50 ohms

### Output 1dB Compression Point Plots

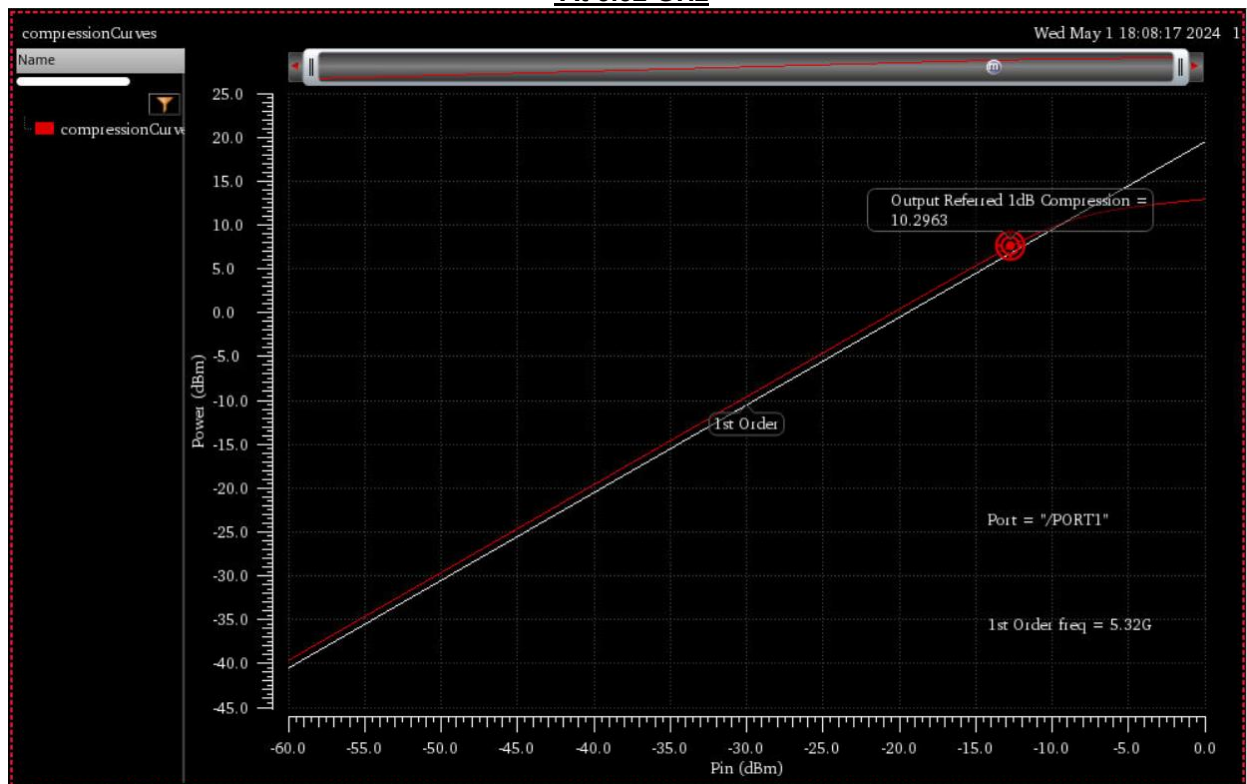
At 5.17 GHz



### At 5.245 GHz

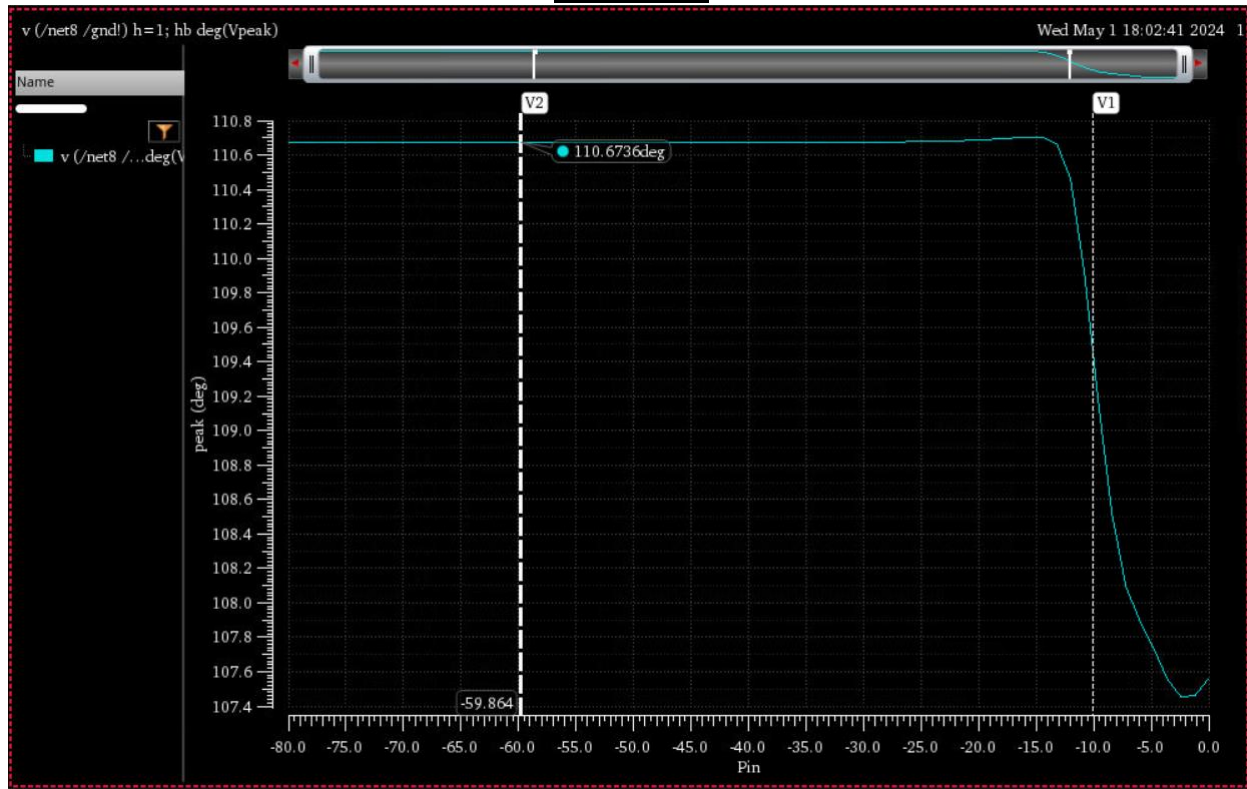


### At 5.32 GHz

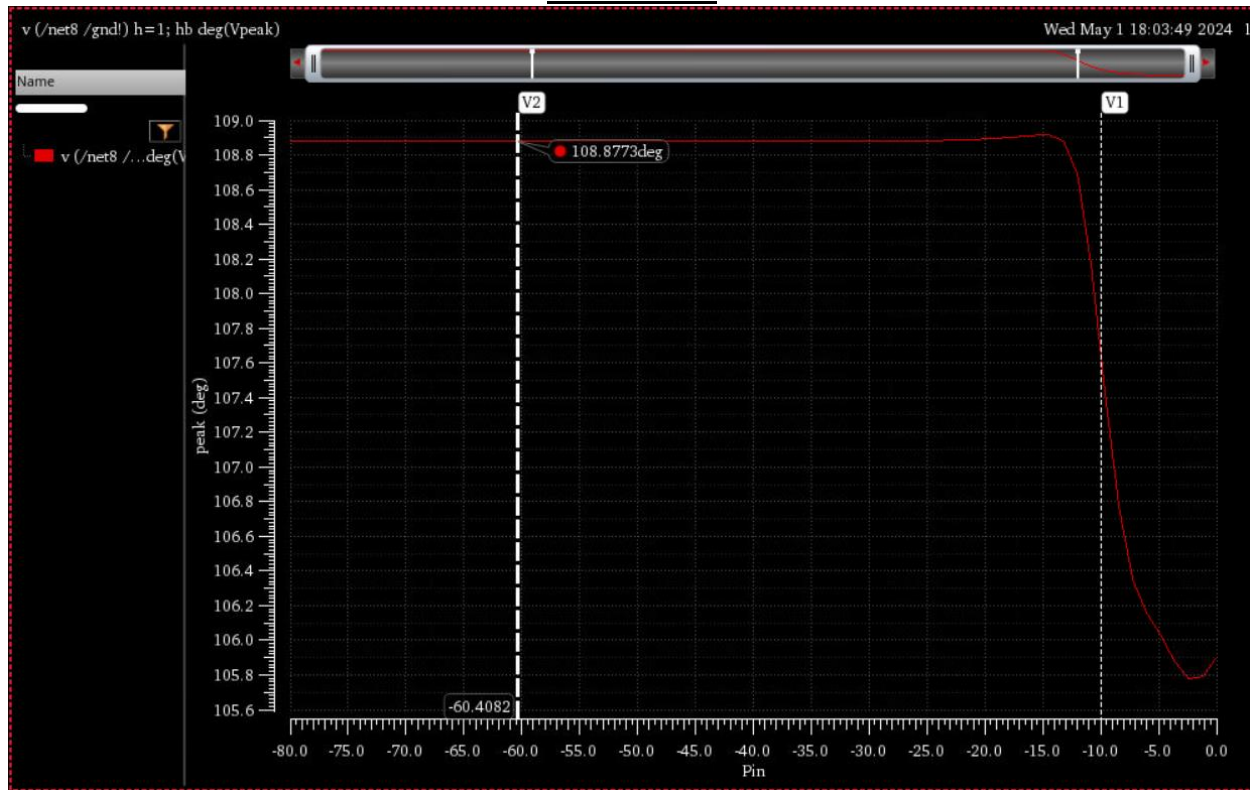


## AM-PM Deviation Plots

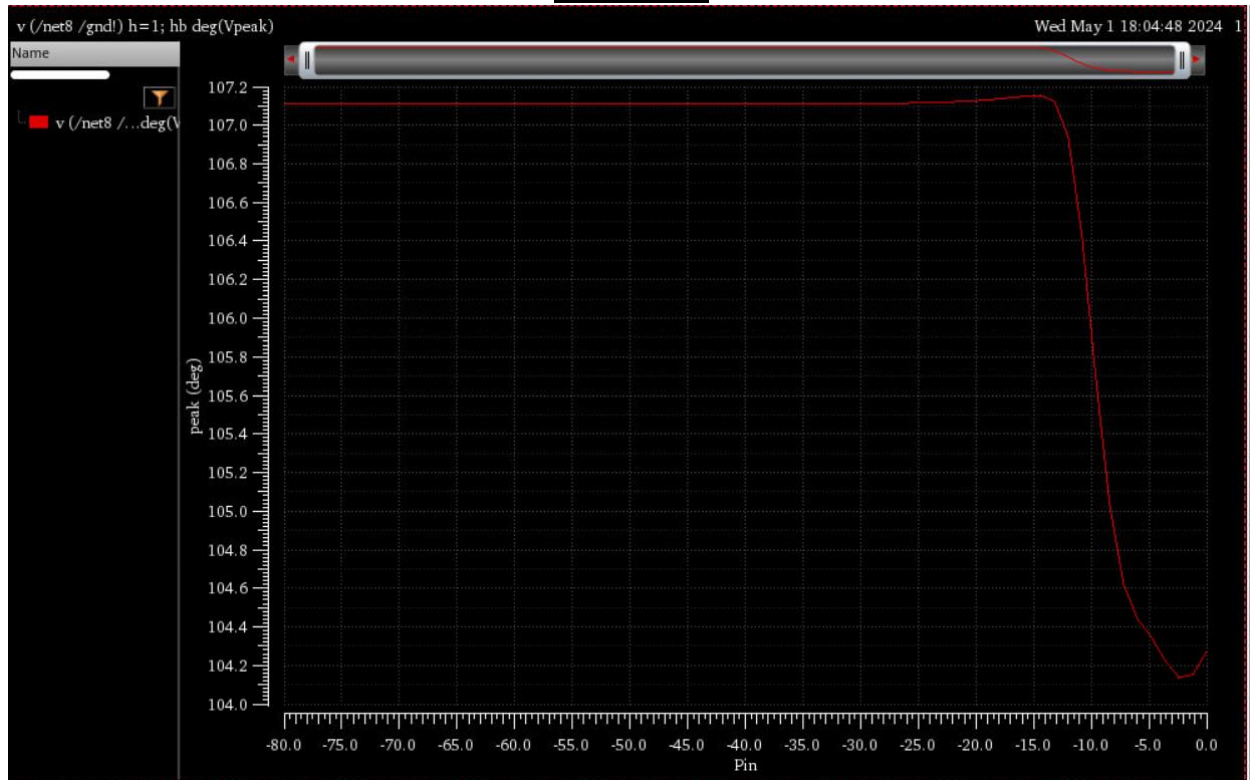
At 5.17 GHz



### At 5.245 GHz

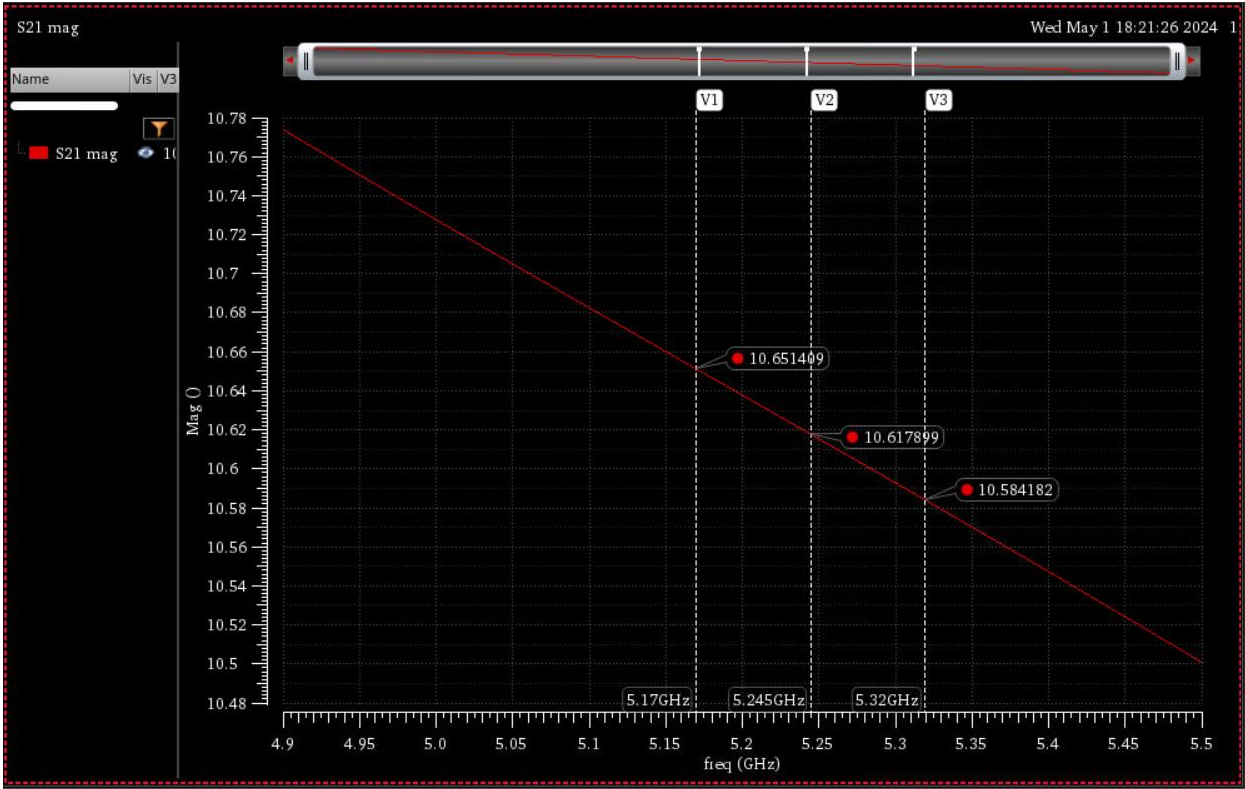


### At 5.32 GHz

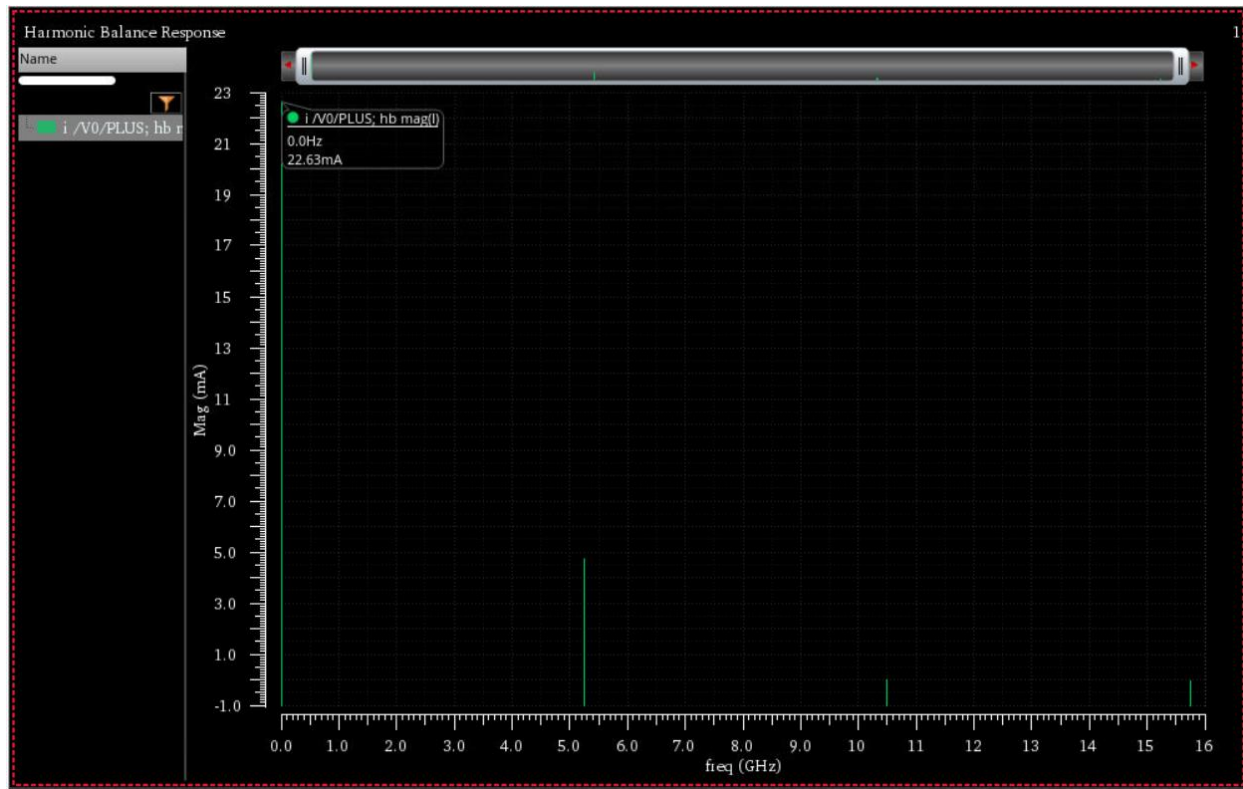




**PA Volatge Gain Plot  
(from Gate to Drain)**



**Current through VDD Plot  
(at 5.245 GHz)**



### Design Procedure

- 1) Down converted the  $R_{load}$  to a lower value of 20 ohms to increase the swing limits at the drain. The Q of the matching network is 1.
- 2) The current through the amplifier mosfet has to be at least more than 20mAs based on the specs given.
- 3) An appropriate bias current of 50uA was chose, the W parameters of the mosfets were decided on that.
- 4) Based on the DC parameters of the cascode mosfet, the value of bias voltage of the cascode mosfet was chosen.
- 5) Then I made slight adjustments to both inductances, as the AM-PM plots were little off.

### Path to Project Files

**Amplifier :** home/ee21b103/cadence\_project/RFIC\_2024/poweramp

**Testbench :** home/ee21b103/cadence\_project/RFIC\_2024/pa\_testbench

**Note:** All the schematic/plots put up here are for reference only. Please replace them with the respective plots/schematic used or obtained by you.